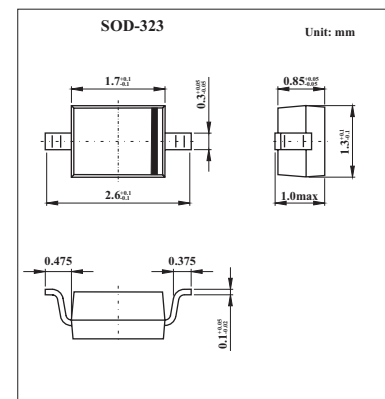


## Schottky barrier Diodes

## 1PS76SB40

## ■ Features

- Low forward voltage
- Guard ring protected
- Very small plastic SMD package
- Low diode capacitance.

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

PARAMETER	SYMBOL	CONDITIONS	MIN	MAX	UNIT
continuous reverse voltage	$V_R$			4	V
continuous forward current	$I_F$			120	mA
repetitive peak forward current	$I_{FRM}$	$t_p \leq 1 \text{ s}; \delta \leq 0.5$		120	mA
non-repetitive peak forward current	$I_{FSM}$	$t_p < 10 \text{ ms}$		200	mA
storage temperature	$T_{stg}$		-65	+150	$^\circ\text{C}$
junction temperature	$T_j$			150	$^\circ\text{C}$
operating ambient temperature	$T_{amb}$		-65	+150	$^\circ\text{C}$

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

PARAMETER	SYMBOL	CONDITIONS	MAX	UNIT
continuous forward voltage	$V_F$	$I_F = 1 \text{ mA}$	380	mV
		$I_F = 10 \text{ mA}$	500	mV
		$I_F = 40 \text{ mA}$	1	V
continuous reverse current	$I_R$	$V_R = 30 \text{ V}; \text{ note 1};$	1	$\mu\text{A}$
		$V_R = 40 \text{ V}; \text{ note 1};$	10	$\mu\text{A}$
diode capacitance	$C_d$	$V_R = 0 \text{ V}; f = \text{MHz};$	5	pF
thermal resistance from junction to ambient	$R_{thj-a}$		450	K/W

Note:

1. Pulse test:  $t_p = 300 \mu\text{s}; \delta = 0.02$ .

## ■ Marking

Marking	s4
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